

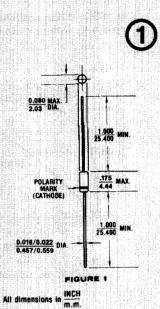
SANTA ANA, CA For more information call: (714) 979-8220 SCOTTSDALE, AZ

DO-35 ★JANS☆

1N962B thru

1N973B

SILICON 400 mW ZENER DIODES



MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed glass case. DO-35.

FINISH: All external surfaces are corrosion resistant and leads solderable.

THERMAL RESISTANCE: 200°C/W (Typical) junction to lead at 0.375-inches from body. Metal-lurgically bonded DO-35's exhibit less than 100°C/W at zero distance from body.

POLARITY: Diode to be operated with the banded end positive with respect to the opposite end.

WEIGHT: 0.2 grams.

MOUNTING POSITION: Any,

FEATURES

- 6.8 TO 200 V ZENER VOLTAGE RANGE
- AVAILABLE IN JAN, JANTX AND JANTXV AND JANS QUALIFICATIONS TO MIL-S-19500/117
- METALLURGICALLY BONDED VOIDLESS DEVICE TYPES
- CONSULT FACTORY FOR VCLTAGES ABOVE 200 V

MAXIMUM RATINGS

Steady State Power Dissipation: 400 mW

Operating and Storage Temperature: -65°C to +175°C

Derating Factor Above 75°C: 4.0 mW/°C Forward Voltage @ 200 mA: 1.5 Volts

* ELECTRICAL CHARACTERISTICS @ 25°C

JEDEC TYPE NUMBER (Note 1:	NOMINAL ZENER VOLTAGE (Note 2: Vz VOLTS	ZENER TEST CURRENT Iz:	MAX. ZENER IMPEDANCE (Note 3) Zz* @ Iz1			MAX. DC ZENER CURRENT (Note 4)	MAX. SURGE CURRENT (RECURRENT) (Note 5: 12 (SURGE)	MAX. REVERSE LEAKAGE CURRENT		MAX. TEMP. COEFFICIENT
			OHMS	OHMS	mA	mA -	mA	,. А	VOLTS	%/°C
1N962B	11	11.5	9.5	700	.25	32	175	5	8.4	+0.076
1N963B	12	10.5	11.5	700	.25	31	160	5	9.1	+0.077
1N964B	13	9.5	13.0	700	.25	28	150	5	9.9	+0.079
1N965B	15	8.5	16	700	.25	25	130	5	11.4	+0.082
1N966B	16	7.8	17	700	.25	24	120	5	12.2	+0.083
1N967B	18	7.0	21	750	.25	20	110	5	13.7	+0.085
1 N968B	20	6.2	25	750	.25	18	100	5	15.2	+0.086
1 N969B	22	5.6	29	750	.25	16	90	5	16.7	+0.087
1N970B	24	5.2	33	750	.25	15	80	5	18.2	+0.088
1N971B	27	4.6	41	750	.25	13	70	5	20.6	+0.090
1N9728	30	4.2	49	1000	.25	12	65	5	22.8	+0.091
1N973B	33	3.8	58	1000	.25	- 11	60	5	25.1	+0.092

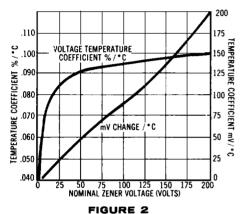
^{*}JEDEC Registered Data

1N962B thru 1N973B DO-35

NOTE 1 The JEDEC type numbers shown (B suffix) have a $\pm 5\%$ tolerance on nominal zener voltage. The suffix A is used to identify $\pm 10\%$ tolerance; suffix C is used to identify $\pm 2\%$; and suffix D is used to identify $\pm 1\%$ tolerance; no suffix indicates $\pm 20\%$ tolerance.

NOTE 2 Zener voltage (V_Z) is measured after the test current has been applied for 20 ± 5 seconds. The device shall be suspended by its leads with the inside edge of the mounting clips between .375" and .500" from the body. Mounting clips shall be maintained at a temperature of 25 + 8/-2°C.

NOTE 3 The zener impedance is derived from the 60 cycle A.C. voltage, which results when an A.C. current



ZENER VOLTAGE TEMPERATURE COEFF. vs. ZENER VOLTAGE

having an R.M.S. value equal to 10% of the D.C. zener current (I_{ZT} or I_{ZK}) is superimposed on I_{ZT} or I_{ZK} . Zener impedance is measured at 2 points to insure a sharp knee on the breakdown curve and to eliminate unstable units.

NOTE 4 The values of I_{ZM} are calculated for a $\pm 5\%$ tolerance on nominal zener voltage. Allowance has been made for the rise in zener voltage above V_{ZT} which results from zener impedance and the increase in junction temperature as power dissipation approaches 400 mW. In the case of individual diodes I_{ZM} is that value of current which results in a dissipation of 400 mW at 50° C lead temperature at 3/8'' from body.

NOTE 5 Surge is 1/2 square wave or equivalent sine wave pulse of 1/120 sec. duration.

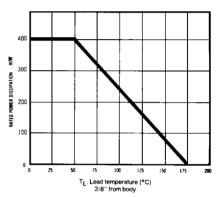
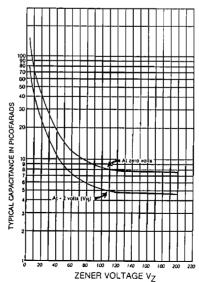


FIGURE 3
POWER DERATING CURVE



CAPACITANCE VS. ZENER VOLTAGE (TYPICAL)